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Here is the copy of the August 30, 2001 1449 form that you requested. The docket is 303.678US4. The serial number is 09/943,393. Please call me if this is not the form that you needed.

David Peterson
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Form 1449*	Atty. Docket No.: 303.678US4	Serial No. Unknown
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Applicant: Kie Y. Ahn et al.	
	Filing Date: Herewith	Group: Unknown

U.S. PATENT DOCUMENTS

**Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
	5,668,035	09/16/1997	Fang, C.H., et al.	438	239	06/10/96
	5,985,725	11/16/1999	Chou, J.	438	294	12/23/97
	6,087,225	07/11/2000	Bronner, G.B., et al.	438	275	02/05/98
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	6,222,788	04/01/2001	Forbes, et al.	365	230.06	

FOREIGN PATENT DOCUMENTS

**Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation Yes / No

OTHER DOCUMENTS
(Including Author, Title, Date, Pertinent Pages, Etc.)

**Examiner Initial	
	Chen, Y., et al., "Performance and Reliability Assessment of Dual-Gate CMOS Devices with Gate Oxide Grown Nitrogen Implanted Si Substrates", International Electron Device Meeting, pg. 1-4, (1997)
	Cho, I.H., et al., "Highly Reliable Dual Gate Oxide Fabrication by Reducing Wet Etching Time and Re-Oxidation for Sub-Quarter Micron CMOS Devices", Extended Abstracts of the 1999 International Conference on Solid State Devices and Materials, pgs. 174-175, (1999)
	Crowder, S., et al., "Trade-offs in the Integration of High Performance Devices with Trench Capacitor DRAM", Dig. Int. Electron Devices Meeting, Washington, D.C., pp. 45-48, (Dec. 1997)
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Examiner	Date Considered

*Substitute Disclosure Statement Form (PTO-1449)

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Sheet 2 of 2

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**Examiner Initial	OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)
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	Ma, T.P., "Making Silicon Nitride film a Viable Gate Dielectric", IEEE Trans. On Electron Devices, 45(3), pp. 680-690, (1998)
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